

Synthesis, structure and properties of CsHSi_3O_7 , a layered silicate with a chiral structure

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Received 3 November 2003; received in revised form 4 February 2004; accepted 4 April 2004

Abstract

The chiral layered silicate CsHSi_3O_7 has been synthesized by hydrothermal techniques, and its structure determined by single crystal X-ray diffraction. The compound crystallizes in the space group $P2_12_12_1$. The silicate single layer consists of both four- and three-connected SiO_4 tetrahedra and may be considered as a member of a series of layer structures with the general formula $(\text{Si}_4\text{O}_9)_m(\text{Si}_2\text{O}_5)_n$. Strong hydrogen bonds occur between the terminal OH^- and O^{2-} ions of neighboring layers. The Cs^+ cations can be ion-exchanged by protons to give a phase of composition $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ with a water molecule occupying the original Cs position, as confirmed by single crystal X-ray diffraction data. The water molecule in $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ can be readily removed without collapse of the crystal structure. Both CsHSi_3O_7 and $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ show SHG (second harmonic generation) efficiencies comparable to that of quartz, and both are not phase-matchable materials.

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Keywords: Cesium silicate; Layered silicate; Chiral structure; Hydrothermal synthesis; Ion-exchange

1. Introduction

Many layered silicates can incorporate functional species in their interlayer space to form nanocomposite materials. The interlayer space serves as a platform of nanometer scale for constructing new materials or tuning material properties by chemical means such as intercalation [1–4]. Organization of the intercalated species is decided by the structure and composition of the host layered lattice. The host lattice usually expands perpendicular to the layers to accommodate the guest species and the layer structure is largely preserved. Layered lattices with non-centrosymmetry are particularly interesting because they can align functional species in a preferred orientation, which is a prerequisite for important physical properties such as non-linear optical activity [5,6]. A prominent example is the recent report of an acentric arrangement of *p*-nitroaniline

molecules intercalated between the layers of kaolinite. The second harmonic generation (SHG) intensity observed for the intercalated hybrid material was found to be substantially higher than that for the original kaolinite host [7]. Layered silicates have also been used for constructing nanoporous materials by metal oxide pillaring or by grafting alkoxy-silyl groups [8–10]. In this aspect, chiral layer lattices are ideal starting points for constructing porous frameworks with chiral symmetry that have potential applications in separations of chiral molecules.

A large number of layered silicates are known and well characterized, though silicates with chiral layered structures are very rare [11–15]. We have been interested in synthesis of microporous materials based on linking silicate layers with other structural units, particularly with transition metal cations [16–18]. As a result of a systematic synthesis study of the effect of reactant composition in CsOH-SiO_2 -transition metal oxide systems using hydrothermal techniques, we obtained a new alkali metal silicate CsHSi_3O_7 that has a layered chiral structure.

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2. Experimental

2.1. Synthesis

Fumed silica (1.3 g, Aldrich, surface area 380 m²/g) preheated at 110°C for 2 h, was dissolved in aqueous CsOH (4.3 ml, 4.24 M, Aldrich). The solution was diluted by adding 1.3 ml deionized water. The pH value of the diluted solution was adjusted to 13.6 with concentrated nitric acid (Merck, 68–70 wt%). The clear solution was subsequently sealed in a Teflon lined Parr autoclave (23 ml inner volume) and heated at 225°C for 3 d under autogenous pressure. After cooling over 4 h the product was recovered by vacuum filtration and washed with water and methanol. The final solution pH was ~11.6. Colorless platy crystals of CsHSi₃O₇ were obtained as a single phase with a maximal crystal size of ca. 0.2 mm. The yield is >80% based on silica.

2.2. Characterization

The crystals were analyzed by EDX using a JEOL JSM 6400 scanning electron microscope with a Link Analytical EXL spectrometer. A Cs:Si atomic ratio close to 1:3 was obtained in agreement with crystal structure refinements. Chemical analyses of the proton ion-exchanged samples were made at Galbraith Laboratories, Knoxville, TN. Thermogravimetric analysis (TGA) was carried out on a TA Instruments Hi-Res 2950 system with a heating rate of 5°C/min in flowing dry N₂ after initially equilibrating the sample at 30°C for 20 min to remove any surface water. Infrared spectra were collected with a Galaxy FTIR 5000 spectrometer using the KBr pellet method in air. To remove surface water, the samples were measured immediately after heating at 50°C for 20 min. UV-Vis-NIR diffuse reflectance spectra were measured with a Cary 500 spectrophotometer on powder samples at room temperature. Powder XRD data were recorded on a SCINTAG XDS2000 automated diffractometer with CuK_α radiation at room temperature with flat plate samples.

2.3. Ion-exchange

Proton ion-exchange experiments were carried out by stirring powder samples in a large excess of 1 M nitric acid at 100°C for 2 d, followed by washing with de-ionized water. Ion-exchanged single crystals were prepared in a similar way but extending the reaction time to 2 weeks and without stirring. After ion-exchange the crystals crashed into tiny platy fragments.

2.4. X-ray crystallography

The crystal structures of CsHSi₃O₇ and the proton-exchanged phase were determined from single crystal X-ray diffraction data collected with a Siemens SMART platform diffractometer equipped with a 1 K CCD area detector. A hemisphere of data (1271 frames at 5 cm detector distance) was collected for each phase using a narrow-frame method with scan widths of 0.3° in ω and an exposure time of 30 s/frame. The first 50 frames were remeasured at the end of data collection to monitor instrument and crystal stability, and the maximum correction applied to the intensities was <1%. The data were integrated using the Siemens SAINT program [19], with the intensities corrected for Lorentz factor, polarization, air absorption, and absorption due to variation in the path length through the detector faceplate. Absorption correction was made using the program SADABS [20]. The structures were solved by direct methods and refined on F^2 by full-matrix least squares using SHELXTL [21]. For CsHSi₃O₇, all non-hydrogen atoms were refined with anisotropic displacement parameters. The hydrogen atom was located from difference maps and was refined isotropically. The crystal quality deteriorated substantially after ion-exchange. As a result, single crystal X-ray data measured on a suitable fragment of the proton-exchanged phase have a high R_{int} value. Crystal quality deterioration is often observed for ion-exchange and intercalation reactions. For the proton-exchanged phase all silicon atoms were refined anisotropically and the oxygen atoms isotropically. Refinements with anisotropic displacement parameters for the oxygen atoms lead to non-positive definite parameters for some sites. The hydrogen atoms were ignored because of the poor data quality and splitting of the water oxygen atom positions. For comparison the absolute structure of the proton-exchanged phase has been kept the same as CsHSi₃O₇, in spite of the high value of the refined absolute structure parameter 1.7(9) for the former. Refinements with a reversed absolute structure model for the proton-exchanged phase showed no change in R -indices. Crystallographic and refinement details are summarized in Table 1. Atom coordinates and selected bond lengths for CsHSi₃O₇ are given in Tables 2–4. Further details of the crystal structure investigation can be obtained from the Fachinformationszentrum Karlsruhe, 76344 Eggenstein-Leopoldshafen, Germany, (fax: (49) 7247-808-666; e-mail: crysdata@fiz.karlsruhe.de) on quoting the depository number CSD 413712 and CSD 413713.

2.5. Second harmonic generation measurements

Powder SHG measurements were performed on a modified Kurtz-NLO system [22]. A Continuum Mini-lite II 1064 nm laser, operating at 1 Hz, was used for all

Table 1
Crystal data and structure refinement details for CsHSi₃O₇ and H₂Si₃O₇·H₂O

| | CsHSi ₃ O ₇ | H ₂ Si ₃ O ₇ ·H ₂ O |
|------------------------------|---|---|
| Formula | H Cs O ₇ Si ₃ | H ₄ O ₈ Si ₃ |
| FW | 330.2 | 216.3 |
| Temperature | 293 K | 293 K |
| Space group | <i>P</i> 2 ₁ 2 ₁ 2 ₁ | <i>P</i> 2 ₁ 2 ₁ 2 ₁ |
| <i>a</i> /Å | 4.9115(3) | 5.041(2) |
| <i>b</i> /Å | 10.3167(7) | 10.507(5) |
| <i>c</i> /Å | 14.1073(9) | 13.924(7) |
| <i>V</i> /Å ³ | 714.82(8) | 737.4(6) |
| Reflections collected/unique | 4386/1645 | 2613/974 |
| <i>R</i> _{int} | 0.0422 | 0.2131 |
| Data/restraints/parameters | 1645/1/105 | 974/0/64 |
| Goodness-of-fit | 1.048 | 1.220 |
| <i>R</i> indices (all data) | <i>R</i> ₁ = 0.0311 | 0.1165 |
| | <i>wR</i> ₂ = 0.0855 | 0.2366 |
| Absolute structure parameter | −0.02(2) | 1.7(9) |

$$R1 = \sum ||F_o| - |F_c|| / \sum |F_o|, wR2 = [\sum (w(F_o^2 - F_c^2)^2) / \sum (wF_o^2)]^{1/2}.$$

Table 2
Atomic coordinates and equivalent isotropic displacement parameters (Å² × 10³) for CsHSi₃O₇

| | <i>x</i> | <i>y</i> | <i>z</i> | <i>U</i> (eq) |
|-------|------------|------------|-----------|---------------|
| Cs | 0.0308(1) | 0.0848(1) | 0.7471(1) | 30(1) |
| Si(1) | −0.3923(2) | 0.2945(1) | 0.9436(1) | 14(1) |
| Si(2) | 0.0172(2) | −0.0829(1) | 0.0089(1) | 13(1) |
| Si(3) | 0.5221(2) | −0.1488(1) | 0.8930(1) | 13(1) |
| O(1) | 0.0529(8) | −0.1961(3) | 0.0860(2) | 23(1) |
| O(2) | −0.2916(6) | −0.0745(3) | 0.9716(2) | 20(1) |
| O(3) | −0.0855(6) | 0.2507(3) | 0.9695(2) | 21(1) |
| O(4) | 0.2079(7) | −0.1100(3) | 0.9179(2) | 21(1) |
| O(5) | 0.1018(7) | 0.0479(3) | 0.0614(3) | 21(1) |
| O(6) | 0.4018(7) | 0.3837(3) | 0.7121(2) | 22(1) |
| O(7) | 0.5236(8) | 0.2366(3) | 0.8431(2) | 24(1) |
| H(1) | 0.47(2) | 0.297(8) | 0.802(6) | 80(30) |

U(eq) is defined as one third of the trace of the orthogonalized *U*_{*ij*} tensor.

Table 3
Atomic coordinates and equivalent isotropic displacement parameters (Å² × 10³) for H₂Si₃O₇·H₂O

| | <i>x</i> | <i>y</i> | <i>z</i> | <i>U</i> (eq) |
|-----------------|------------|------------|-----------|---------------|
| Si(1) | −0.2756(9) | 0.2982(3) | 0.9468(3) | 20(1) |
| Si(2) | 0.131(1) | −0.0826(3) | 0.0013(3) | 20(1) |
| Si(3) | 0.6309(9) | −0.1595(3) | 0.8919(3) | 19(1) |
| O(1) | 0.157(3) | −0.1914(9) | 0.0825(6) | 29(3) |
| O(2) | −0.167(2) | −0.0809(8) | 0.9561(7) | 27(3) |
| O(3) | 0.019(3) | 0.260(1) | 0.9757(7) | 32(3) |
| O(4) | 0.336(3) | −0.1098(9) | 0.9179(7) | 32(3) |
| O(5) | 0.189(2) | 0.0506(8) | 0.0545(6) | 23(2) |
| O(6) | 0.306(2) | 0.3584(9) | 0.7201(7) | 30(3) |
| O(7) | 0.665(3) | 0.248(1) | 0.8403(8) | 39(3) |
| O(8 <i>wa</i>) | −0.112(7) | 0.082(2) | 0.717(2) | 44(5) |
| O(8 <i>wb</i>) | −0.012(9) | 0.081(3) | 0.754(3) | 44(5) |

U(eq) is defined as one third of the trace of the orthogonalized *U*_{*ij*} tensor.

Table 4
Selected bond lengths [Å] for CsHSi₃O₇

| | |
|-------------|----------|
| Si(1)–O(7) | 1.593(3) |
| Si(1)–O(3) | 1.615(3) |
| Si(1)–O(3) | 1.618(3) |
| Si(1)–O(5) | 1.628(3) |
| Si(2)–O(5) | 1.594(3) |
| Si(2)–O(1) | 1.605(3) |
| Si(2)–O(2) | 1.608(3) |
| Si(2)–O(4) | 1.614(4) |
| Si(3)–O(6) | 1.565(3) |
| Si(3)–O(2) | 1.630(3) |
| Si(3)–O(4) | 1.633(3) |
| Si(3)–O(1) | 1.634(3) |
| O(7)–H(1) | 0.89(2) |
| O(6)···H(1) | 1.59(3) |
| O(7)···O(6) | 2.465(5) |
| Cs–O(6) | 3.025(3) |
| Cs–O(7) | 3.185(4) |
| Cs–O(7) | 3.239(4) |
| Cs–O(4) | 3.256(3) |
| Cs–O(1) | 3.265(4) |
| Cs–O(5) | 3.463(3) |
| Cs–O(6) | 3.522(4) |
| Cs–O(6) | 3.616(3) |
| Cs–O(3) | 3.620(3) |

measurements. Because the SHG efficiency of powders has been shown to depend strongly on the particle size [23], the samples were ground and sieved into distinct particle size ranges, <20, 20–45, 45–63, 63–75, 75–90, and 90–125 μm. To make relevant comparisons with known SHG materials, polycrystalline quartz was also ground and sieved into the same particle-size ranges. All of the powders were placed in separate capillary tubes. The SHG light, i.e., 532 nm green light, was collected in reflection and detected by a photomultiplier tube (Oriel Instruments). To detect only the SHG light, a 532 nm narrow band-pass interference filter was attached to the tube. A digital oscilloscope (Tektronix TDS 3032) was used to view the SHG signal.

3. Results and discussion

3.1. The crystal structure

CsHSi₃O₇ crystallizes in the orthorhombic system with space group symmetry *P*2₁2₁2₁. There are three different tetrahedral silicon sites (Fig. 1). Si(1) and Si(3) are each bonded to three bridging oxygen atoms and a terminal oxygen atom, while Si(2) is bonded to four bridging oxygen atoms. The terminal oxygen atom O(7) of the the Si(1)O₄ tetrahedron is bonded to a proton to form a silanol group. The shortest Si–O bond length

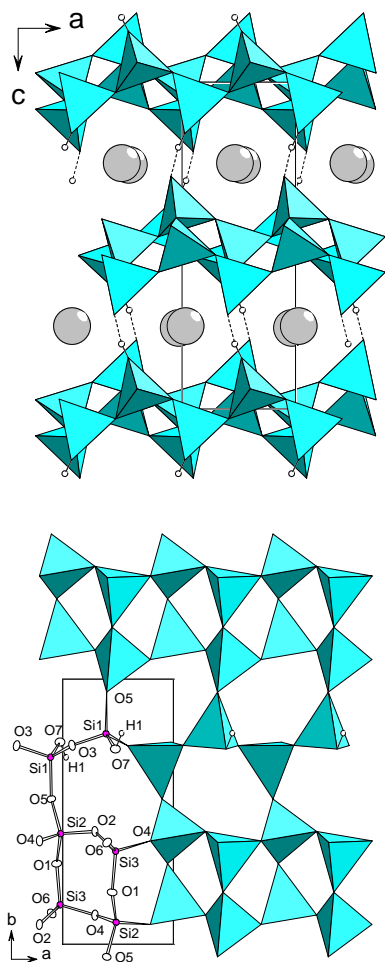


Fig. 1. The structure of CsHSi_3O_7 viewed along $[010]$ (top) and the HSi_3O_7 layer (bottom). Dashed lines represent hydrogen bonds. Gray circles represent Cs atoms.

(1.565 Å) is found, as expected, for the terminal Si(3)–O(6) bond. The Si(2,3)O₄ tetrahedra are linked to form 4-member rings that are interconnected to form double chains parallel to $[100]$, while the Si(1)O₄ tetrahedra are linked to form single chains also along $[100]$. The single chains of Si(1)O₄ tetrahedra and the double chains of Si(2,3)O₄ tetrahedra are cross-linked alternatively to form a single layer by sharing the O(5) corners. Six-ring voids are outlined by the linking of the single and double chains. The single layers are stacked along the $[001]$ direction and neighboring layers are related by 2_1 screw axes. Very short hydrogen bonds occur between the terminal silanol groups of one layer and the terminal O(6) atoms of the neighboring layers (O(6)⋯O(7): 2.465 Å, Table 4). The negative charge of the HSi_3O_7 single layers is balanced by the interlayer Cs^+ cations. There are nine oxygen atoms surrounding the Cs atom with Cs–O distances in the range 3.025–3.620 Å. The three shortest Cs–O bonds are formed with the terminal O(6) and O(7) atoms. The CsO_9 polyhedron is highly

irregular with the Cs atom strongly shifted from the center to one side.

The double chains of the Si_3O_7 layer in CsHSi_3O_7 are also found in the recently reported one-dimensional structure of CsHSi_2O_5 (Fig. 2d) [11]. The closely related compounds KHSi_2O_5 [24] and $\text{NaHSi}_2\text{O}_5 \cdot 2\text{H}_2\text{O}$ [25] have silicate layers that may be considered as forming from cross-linking only the single chains of CsHSi_3O_7 . In the Si_3O_7 layer of CsHSi_3O_7 the ratio of single chains to double chains is 1:1. By varying this ratio a series of layered silicate anions with the general formula $(\text{Si}_4\text{O}_9)_m(\text{Si}_2\text{O}_5)_n$ may be generated. The Si_3O_7 layer represents the member of the series with $m = n = 1$. The Si_2O_5 layer of KHSi_2O_5 is an end member with $m = 0$, $n = \text{infinite}$. The other end member layer with $m = \text{infinite}$, $n = 0$, is found in the layered structure of $\text{K}_2\text{Si}_4\text{O}_9$ [26] in which the double chains are directly linked to each other to form one column of 6-rings between neighboring double chains (Fig. 2c). The ratio of 6- to 4-rings in the layers of each member of the series is $(m + n)/(2m)$ while the ratio of 4- and 3-connected tetrahedra (Q^4/Q^3) equals to $m/(m + n)$. The general formula should be helpful in finding new materials since the layer structure and charge of each member of the series is readily predicted.

Strong hydrogen bonds ($d_{(\text{O} \cdots \text{O})} < 2.50 \text{ \AA}$) [27] are also found in the structures of AHSi_2O_5 , $A = \text{K}, \text{Cs}$ [11,24]. A common feature in these two compounds and CsHSi_3O_7 is that the oxygen atoms forming the hydrogen bonds are terminal corners of three-connected SiO_4 tetrahedra. According to a statistical study of silicate minerals containing silanol groups, Si–OH bond length decreases as the connectedness of the SiO_4 tetrahedron increases [28]. In three-connected tetrahedra the Si–OH bonds tend to be shorter than the three bridging Si–O bonds. The shorter Si–OH bond implies that the more negative charge of the O atom is polarized towards Si, thus increasing the tendency of the OH group to form strong hydrogen bond. On the other hand, the residual charge of the terminal O^{2-} corners of the SiO_4 tetrahedra is large, and is not readily balanced by the large monovalent cations in these structures. Therefore, both the terminal O atom and the OH group in these structures favor strong hydrogen bonds. The O–H⋯O

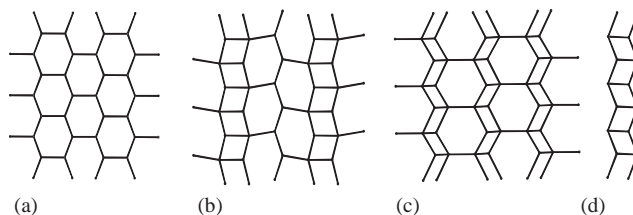


Fig. 2. Structures of the layer series $(\text{Si}_4\text{O}_9)_m(\text{Si}_2\text{O}_5)_n$. (a) The layer of KHSi_2O_5 with $m = 0$, $n = \text{infinite}$, (b) the layer of CsHSi_3O_7 with $m = n = 1$, (c) the layer of $\text{K}_2\text{Si}_4\text{O}_9$ with $m = \text{infinite}$, $n = 0$, and (d) the double chain of CsHSi_2O_5 . Each node represents a SiO_4 tetrahedron.

angle in CsHSi_3O_7 is very close to the average value of 167° found in other inorganic structures [28].

3.2. Ion-exchange

Preliminary experiments showed that at room temperature the Cs^+ cations of CsHSi_3O_7 are not readily exchanged by protons. However, at 100°C the ion-exchange process occurs easily. After proton ion-exchange, elemental analysis gave 1.68% H, 39.69% Si and $<0.29\%$ Cs. The results show almost complete removal of the Cs^+ cations (<0.002 Cs per Si atom) and correspond to the composition $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ (calc. 1.85% H, 39.01% Si). The powder X-ray diffraction patterns measured before and after ion-exchange were compared with the simulated patterns. As shown in Fig. 3, the agreement between observed and simulated patterns is good. The simulated patterns were calculated from single crystal structure data with the program PowderCell [29]. Preferred orientation along the (001) plane was apparent and was compensated in the

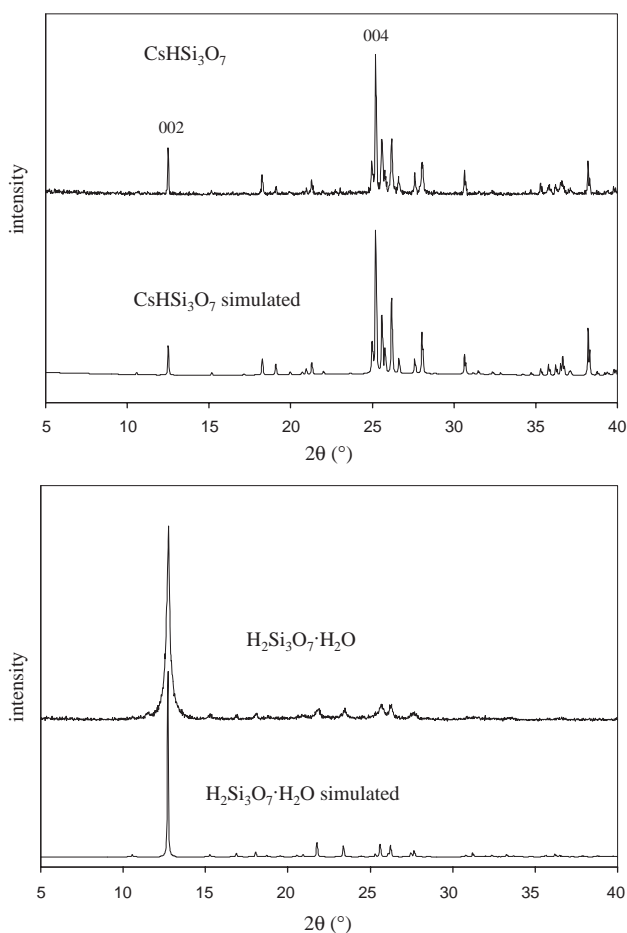


Fig. 3. Observed and simulated powder X-ray diffraction data for CsHSi_3O_7 (top) and $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ (bottom). Preferred orientation along (001) was compensated for the simulated patterns [29,30].

simulated patterns for both phases [30]. The crystal structure of $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ determined from single crystal data is essentially the same as CsHSi_3O_7 with interlayer water molecules occupying the original Cs positions (Fig. 4). The Si(3)–O(6) bond length increases from 1.565 Å in CsHSi_3O_7 to 1.603 Å in $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ due to protonation of the terminal O(6) atom. The O(6)...O(7) distance increases from 2.465 Å in CsHSi_3O_7 to 2.72 Å in $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$, indicating significant weakening of the interlayer hydrogen bonds in the latter. The interlayer water oxygen site of $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ is split into two positions O(8wa) and O(8wb) which are 0.72 Å apart from each other with occupancies 0.58(4) for O(8wa) and 0.42(4) for O(8wb). Both water oxygen positions are at favorable distances to form hydrogen bonds to the terminal O(6) and O(7) atoms (Fig. 4b).

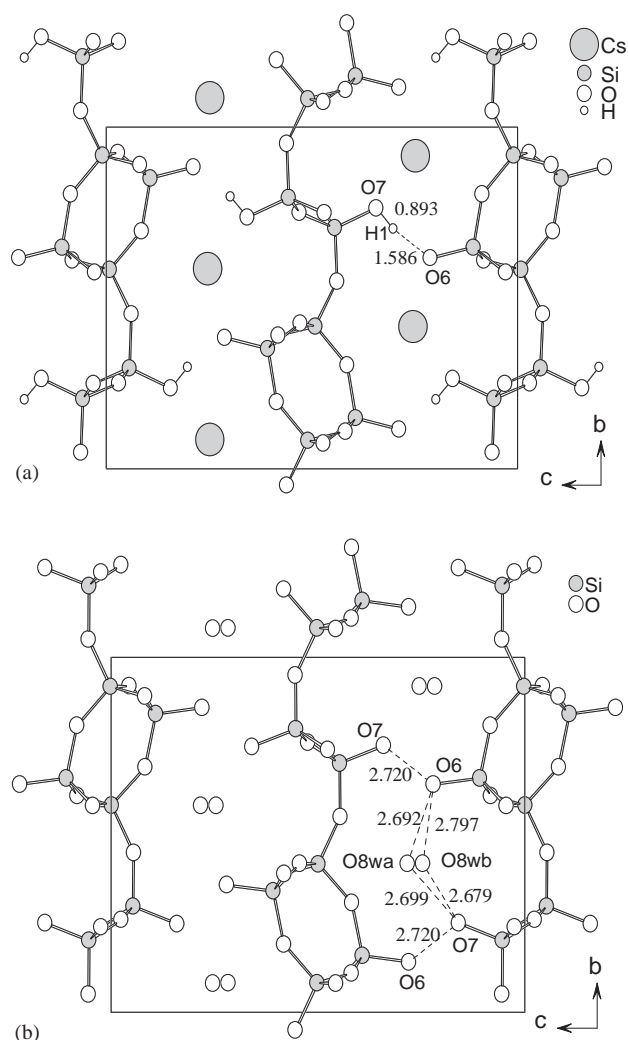


Fig. 4. The structure of CsHSi_3O_7 (a) and $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ (b) viewed along [100]. Atom distances are marked in angstroms.

3.3. TGA

TGA data measured between 30°C and 1000°C for the proton-exchanged sample show a sharp weight loss that starts immediately upon heating and ends at ~120°C. A second weight-loss starts at ~250°C and ends at ~650°C. The observed weight-loss of 8.39% below 120°C corresponds to dehydration of the sample (theor. 8.33% for $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$). The total weight-loss of 6.8% between 250°C and 650°C is less than the theoretical value of 8.33% for a complete dehydroxylation, indicating that part of the hydroxyl groups were trapped in the residue. The residue was shown to be amorphous by powder X-ray diffraction. Infrared data measured for the residue show a weak broad band at 3435 cm^{-1} due to the stretching vibrations of the trapped OH groups. Si–OH groups have been observed in silicate glasses treated at temperatures over 1000°C [31]. A proton-exchanged sample heated at 150°C for 45 min was examined with X-ray powder diffraction. The diffraction patterns were closely similar before and after heating, which indicates that dehydration did not cause substantial changes of the structure.

TGA data for CsHSi_3O_7 show a sharp weight loss of 2.2% between 500°C and 600°C. The residue was shown to be amorphous by powder X-ray diffraction data. The observed weight loss is less than the theoretical value of 2.73% for a complete dehydroxylation, due to retention of some Si–OH groups in the residue.

3.4. Spectroscopy

Fig. 5 shows the infrared spectra for both the original and the proton-exchanged samples. For CsHSi_3O_7 the strong bands in the region $950\text{--}1300\text{ cm}^{-1}$ are usually believed to be due to asymmetric stretching vibrations of Si–O–Si linkages and stretching vibrations of terminal Si–O bonds. The bands between 400 and 800 cm^{-1} are associated with the symmetric stretching vibrations of Si–O–Si bridges [32]. For strong O–H...O hydrogen bonds $\nu(\text{OH})$ shifts to low wave number regions as the O...O distance decreases. The $\nu(\text{OH})$ band of CsHSi_3O_7 is expected in the range $800\text{--}1200\text{ cm}^{-1}$ from the short O(7)...O(6) distance of 2.465 \AA [27], which is not resolved from Si–O vibration bands. For the proton-exchanged sample $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ the bending mode of water molecules is observed at 1624 cm^{-1} . Stretching vibrations of OH groups $\nu(\text{OH})$ are observed between 3000 and 3700 cm^{-1} . The broad low frequency bands are related to the disordered interlayer water molecules. The sharp high frequency band at 3658 cm^{-1} can be assigned to the terminal OH groups that are involved in much weakened hydrogen bonding [32,33].

The UV-Vis-NIR diffuse reflectance spectra are shown in Fig. 6. The absorption band observed in the spectrum of $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ at $\sim 1400\text{ nm}$ (7150 cm^{-1}) is

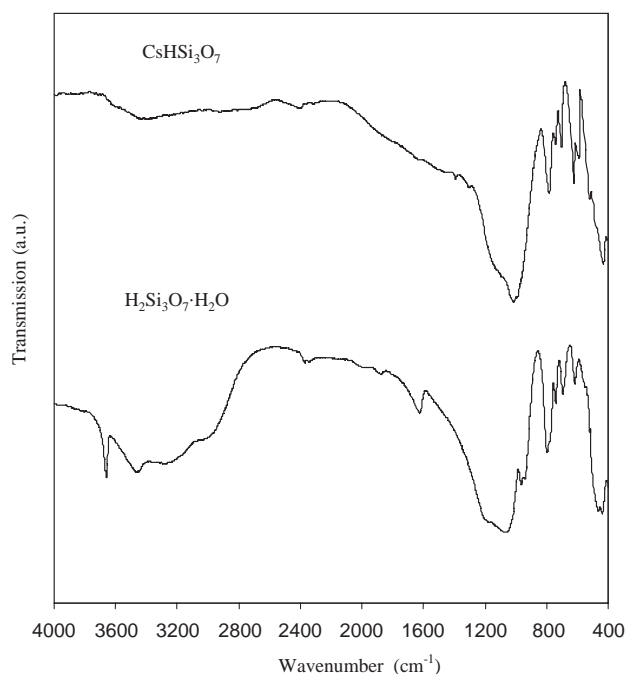


Fig. 5. The infrared spectra of CsHSi_3O_7 and $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$.

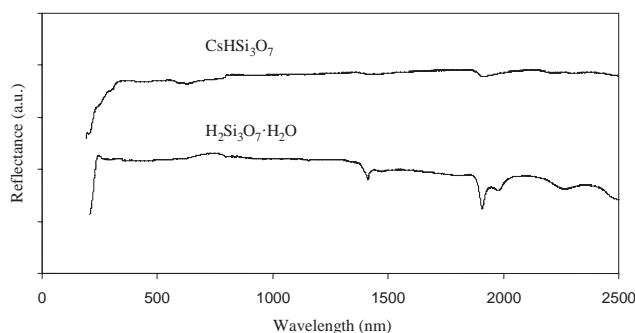


Fig. 6. The diffuse reflectance spectra of CsHSi_3O_7 and $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$.

related to the first overtone of the fundamental stretching vibration of the hydroxyl groups. The absorption bands near 1900 nm are associated with combinations of bending and stretching vibrations of water molecules [34].

3.5. Second-order NLO properties

Powder SHG measurements on sieved polycrystalline CsHSi_3O_7 revealed a SHG efficiency comparable to that of quartz. For a non-phase-matchable material the SHG intensity decreases as the particle size becomes substantially larger than the coherence length of the materials. As can be seen from Fig. 7, both CsHSi_3O_7 and the proton-exchanged phase $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ are not phase-matchable. The SHG active feature of $\text{H}_2\text{Si}_3\text{O}_7 \cdot \text{H}_2\text{O}$ confirms that the ion-exchange process did not destroy

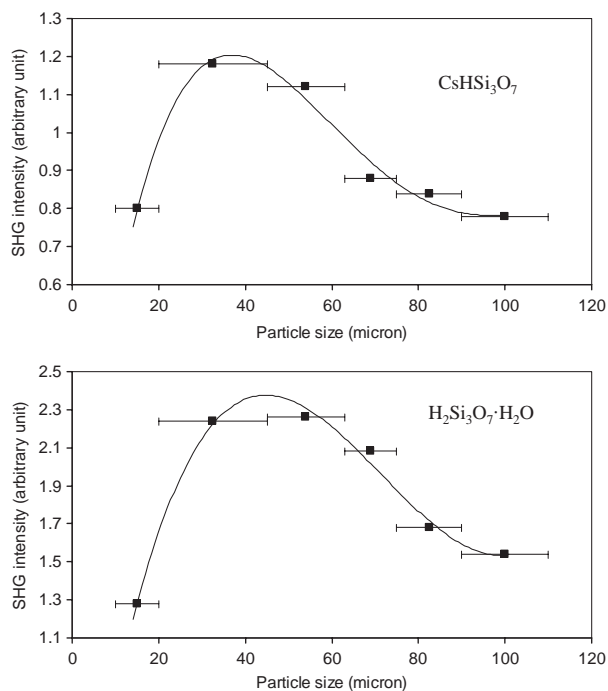


Fig. 7. SHG data for CsHSi₃O₇ (top) and H₂Si₃O₇·H₂O (bottom).

the non-centrosymmetric character of the original structure.

Acknowledgments

We thank Dr. P. S. Halasyamani and Dr. K. Ok for their help in the SHG measurements and the National Science Foundation (DMR-0120463), the R.A. Welch Foundation for financial support. This work made use of Shared Experimental Facilities of the Center for Materials Chemistry (CMC-UH) at the University of Houston.

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